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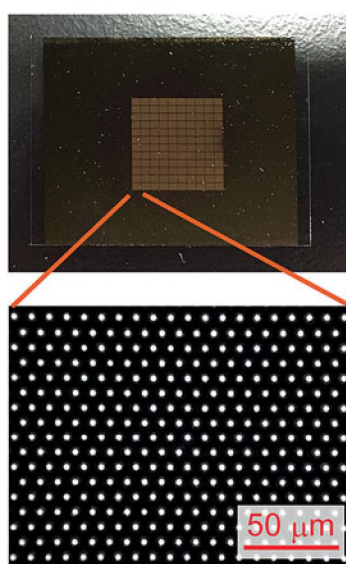
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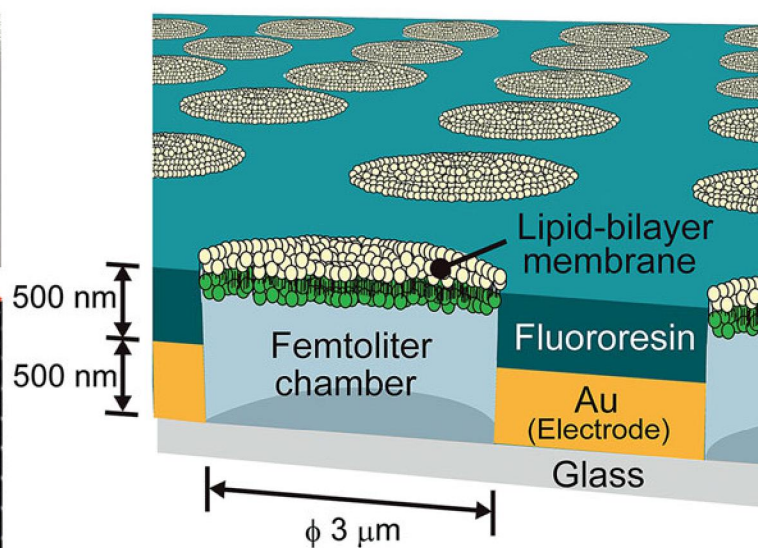
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ANNOUNCEMENTS

About the cover: ALBiC with nano-sized electrode (el-ALBiC). (a) A bright-field image of the through-hole structures on a fabricated nano-device. (b) Schematic illustration of el-ALBiC that displays through-hole structures ($\phi = 3 \mu\text{m}$) on a double layer of fluororesin ($h = 500 \text{ nm}$) and Au ($h = 500 \text{ nm}$). Individual orifices on through-hole structures are sealed with lipid-bilayer membranes. See “Novel Nano-Device to Measure Voltage-Driven Membrane Transporter Activity,” by Watanabe *et al.*, p. 70.